



# P-Channel -40V (D-S) Power MOSFET

#### **Features**

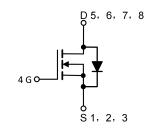
- 100% Avalanche Tested
- Extremely Low Losses with Low FOM Rdson\*Qg
- Halogen Free, Pb-Free
- RoHS Compliant



#### **PDFN5060**

## **Applications**

- DC-DC
- Motors, lamps
- Power switching



| Absolute Maximum Ratings (T <sub>J</sub> =25°C unless otherwise noted) |                      |                 |             |      |  |
|--|----------------------|-----------------|-------------|------|--|
| Parameter  |                      | Symbol          | Value       | Unit |  |
| Drain Source Voltage   |                      | V <sub>DS</sub> | -40         | V    |  |
| Gate Source Voltage  |                      | $V_{GS}$        | ±20         | V    |  |
| Drain Current, Continuous V <sub>GS</sub> =-10V <i>(Note 1)</i>        | T <sub>C</sub> =25°C | I <sub>D</sub>  | -25         | А    |  |
| Drain Current, Pulsed (Note 2)   |                      | I <sub>DM</sub> | -100        | А    |  |
| Single Avalanche Energy@ L=0.3mH                                       |                      | E <sub>AS</sub> | 141         | mJ   |  |
| Power Dissipation(Note 3) T <sub>C</sub> =25°C                         |                      | P <sub>D</sub>  | 35          | W    |  |
| Operating Junction/ Storage Temperature Range                          |                      | TJ/ Tstg        | -55 to +150 | °C   |  |

Note 1: Calculated continuous current based on maximum allowable junction temperature.

Note 2: Repetitive rating; pulse width limited by max. junction temperature.

| Thermal Characteristics             |                   |     |      |  |  |
|-------------------------------------|-------------------|-----|------|--|--|
| Parameter                           | Symbol            | Max | Unit |  |  |
| Thermal Resistance Junction to Case | R <sub>thJC</sub> | 3.6 | °C/W |  |  |

Note 3: The power dissipation PD is based on max. junction temperature, using junction-to-case thermal resistance.



| Electrical Characteristics (T <sub>J</sub> =25°C unless otherwise noted) |                      |  |     |      |      |      |
|--|----------------------|--|-----|------|------|------|
| Parameter  | Symbol               | Test Conditions  | Min | Тур  | Max  | Unit |
| Drain-Source Breakdown Voltage   | V <sub>(BR)DSS</sub> | V <sub>GS</sub> =0V, I <sub>D</sub> =-250μA                | -40 |      |      | V    |
| Zero Gate Voltage Drain Current  | I <sub>DSS</sub>     | V <sub>DS</sub> =-60V, V <sub>GS</sub> =0V                 |     |      | -1   | uA   |
| Gate Threshold Voltage   | V <sub>GS(TH)</sub>  | V <sub>DS</sub> =V <sub>GS</sub> , I <sub>DS</sub> =-250uA | -1  |      | -2.5 | V    |
| Gate Leakage Current   | I <sub>GSS</sub>     | V <sub>GS</sub> =±20V, V <sub>DS</sub> =0V                 |     |      | ±100 | nA   |
| Drain-Source On-state  | Б                    | V <sub>GS</sub> =-10V, I <sub>D</sub> =-10A                |     | 10   | 15   | · mΩ |
| Resistance   | R <sub>DS(on)</sub>  | V <sub>GS</sub> =-4.5V, I <sub>D</sub> =-8A                |     | 13   | 22   |      |
| Total Gate Charge  | Qg                   |  |     | 18   |      |      |
| Gate-Source Charge   | Q <sub>gs</sub>      | I <sub>D</sub> = -10A,<br>V <sub>DS</sub> =-32V,           |     | 9    |      | nC   |
| Gate-Drain Charge  | $Q_{gd}$             | V <sub>GS</sub> = -4.5V                                    |     | 8    |      |      |
| Turn-on Delay Time   | t <sub>d(on)</sub>   |  |     | 19   |      |      |
| Turn-on Rise Time  | t <sub>r</sub>       | V <sub>GS</sub> =-10V, V <sub>DD</sub> =-20V,              |     | 77   |      |      |
| Turn-off Delay Time  | t <sub>d(off)</sub>  | $I_D$ =-20A, $R_G$ =3 $\Omega$                             | 48  |      | ns   |      |
| Turn-off Fall Time   | t <sub>f</sub>       |  |     | 59   |      |      |
| Input Capacitance  | C <sub>iss</sub>     |  |     | 3468 |      |      |
| Output Capacitance   | Coss                 | V <sub>GS=</sub> 0V, V <sub>DS</sub> =-25V, f=1MHz         |     | 210  |      | pF   |
| Reverse Transfer Capacitance   | C <sub>rss</sub>     |  |     | 202  |      |      |

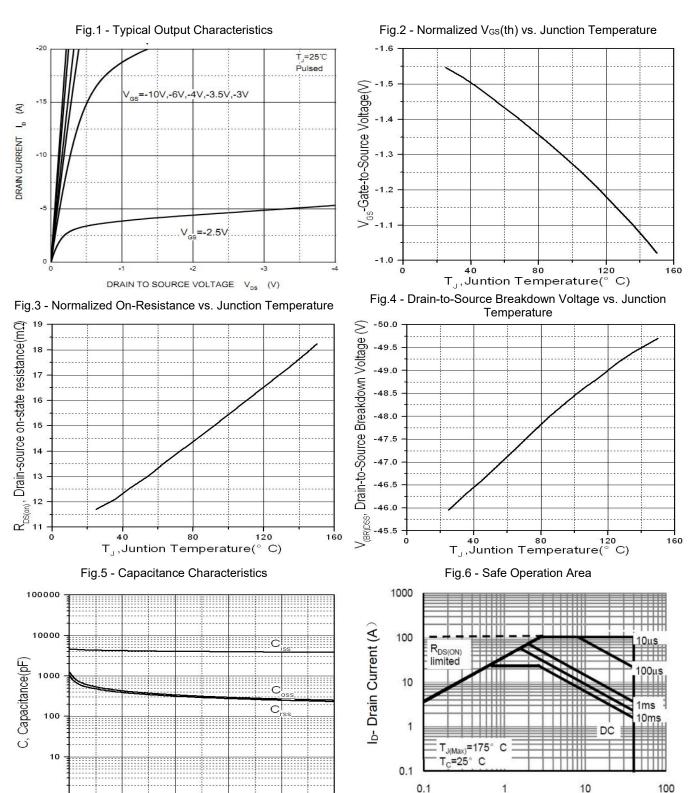
| Reverse Diode Characteristics (T <sub>J</sub> =25°C unless otherwise noted) |                 |  |     |     |      |      |
|---|-----------------|--|-----|-----|------|------|
| Parameter   | Symbol          | Test Conditions                          | Min | Тур | Max  | Unit |
| Forward Current, Continuous   | I <sub>SD</sub> | T <sub>C</sub> =25°C                     |     |     | -25  | Α    |
| Pulsed Source Current   | I <sub>SM</sub> | T <sub>C</sub> =25°C                     |     |     | -100 | Α    |
| Diode Forward Voltage   | V <sub>SD</sub> | I <sub>F</sub> =-1A, V <sub>GS</sub> =0V |     |     | -1.3 | V    |



Vds Drain-Source Voltage (V)



## **Typical Characteristics Curves** (T<sub>J</sub> = 25°C unless otherwise noted)

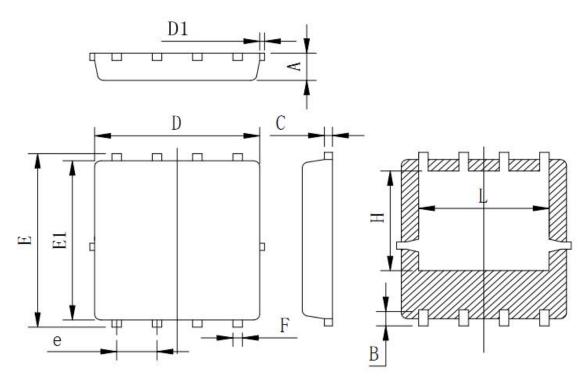


V<sub>DS</sub>, Drain-to-Source Voltage (V)



# Package Outline Dimensions (Unit: millimeters)

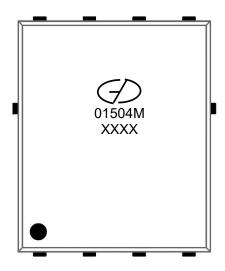
## **PDFN5060**



| Symbol | Min  | Тур   | Max  |
|--------|------|-------|------|
| A      | 0.90 | 0.95  | 1.00 |
| В      | 0.48 | 0.58  | 0.68 |
| С      | 0.20 | 0.254 | 0.30 |
| D      | 5.00 | 5.20  | 5.40 |
| D1     |      |       | 0.15 |
| Е      | 5.90 | 6.05  | 6.20 |
| El     | 5.40 | 5.55  | 5.70 |
| e      | 1.22 | 1.27  | 1.32 |
| F      | 0.25 | 0.30  | 0.35 |
| Н      | 3.27 | 3.47  | 3.67 |
| L      | 3.80 | 4.00  | 4.20 |



# **Marking Outline**



Part Name: GMP01504M

1. Logo Mark:



2. P/N Mark: 01504M

3. Date Code: XXXX

4. Pin 1#: ●



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